

# 400mA Synchronous Step-down DC/DC Module with MODE pin and Inductor

No.EA-592-231209

#### OVERVIEW

The RM590L is a synchronous, step-down DC/DC converter which delivers up to 400mA of output current. The RM590L can be configured for either PWM/VFM automatic shift operation or forced PWM operation by controlling of MODE pin. This device has a built-in inductor ( $0.5\mu$ H, DCR= $0.125\Omega$  (TYP)) and is available in 2.2 (mm) x 2.0 (mm) x 1.5 (mm) sized QFN2220-8 package for high density mounting. Therefore, it is possible to save space in the mounting area.

#### **KEY BENEFITS**

- Having an inductor built-in, it is possible to simplify the board design and reduce the mounting area.
- PWM/VFM automatic shift operation provides high efficiency at light loads.
- Having an inductor built-in, the number of parts can be reduced, and the man-hours for managing purchased parts can be reduced (concern about EOL).

#### **TYPICAL CHARACTERISTICS KEY SPECIFICATIONS** Efficiency Input Voltage Range (Maximum Rating): V<sub>OUT</sub>=1.8V 2.3 V to 5.5 V (6.5 V) 100 90 VFM / PWM A Output Voltage (Fixed Output Voltages): 80 from 0.6V to 3.3V in 0.1V increments 70 ±1.5% (V<sub>SET</sub> ≥ 1.2 V), ±18 mV (V<sub>SET</sub> < 1.2 V) Efficiency n [%] 50 Output Voltage Accuracy 40 30 Output Voltage (Adjustable Output Voltages): 20 0.6 V to 5.5 V 0.6V Reference (VFB), ±9 mV Voltage Accuracy 100 1000 \_ [mA] Selectable Oscillator Frequency: Typ. 6.0 MHz TYPICAL APPLICATIONS Oscillator Maximum Duty: Min. 100% MOSFET ON Resistance (VIN = 3.6 V): Vоит High Side MOSFET Typ. 0.245 Ω Low Side MOSFET Typ. 0.225 Ω VOUT 🛛 Cour MODE Control UVLO Detector Threshold: Typ. 2.0 V Soft-start Time: Typ. 0.15 ms IX CE CE Control Thermal Shutdown Function: Detection Temperature 140°C Fixed Output Voltage Type (RM590Lxx2A/B) Release Temperature 100°C PACKAGE **MODE** VFB X RM590L MODE Control R<sub>2</sub> QFN2220-8 **CE** GND X CE Control 2.2 x 2.0 x 1.5 (mm) Adjustable Output Voltage Type (RM590L002C/D)

#### APPLICATIONS

- Devices need to be miniaturized such as wearables, hearables
- Phones, domestic LAN systems
- Communication modules, and applications for Industrial equipment
- Instrumentation equipment such as flow meters and pressure gauges

# **SELECTION GUIDE**

The set output voltage, the output voltage type, and the auto-discharge function are user-selectable options.

### **Selection Guide**

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
RM590Lxx2\$-TR	QFN2220-8	2,000	Yes	Yes

xx : Set Output Voltage (V<sub>SET</sub>)

Fixed Output Voltage Type : 06 to 33 (0.6 V to 3.3 V, 0.1 V steps)

The voltage in 0.05 V step is shown as follows.

Ex. 1.25 V: RM590L122\$5

Refer to Product-specific Electrical Characteristics for details.

Adjustable Output Voltage Type : 00

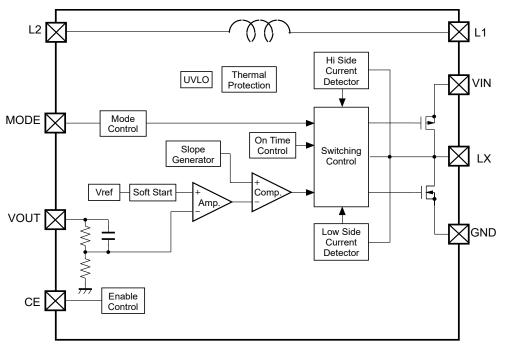
\$ : Versions

\$	Output Voltage Type	Auto-discharge Function	V <sub>SET</sub>
А	Fixed	No	
В	Fixed	Yes	0.6 V to 3.3 V
С	Adjustable	No	
D	Adjustable	Yes	0.6 V to 5.5 V

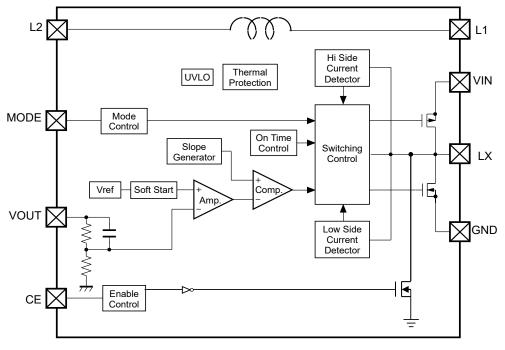
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# **BLOCK DIAGRAMS**

RM590Lxx2A/B (Fixed Output Voltage Type)

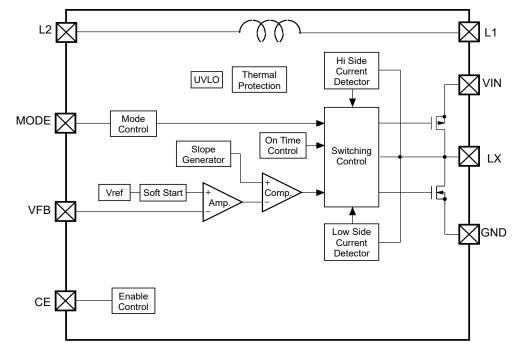


### RM590Lxx2A Block Diagram



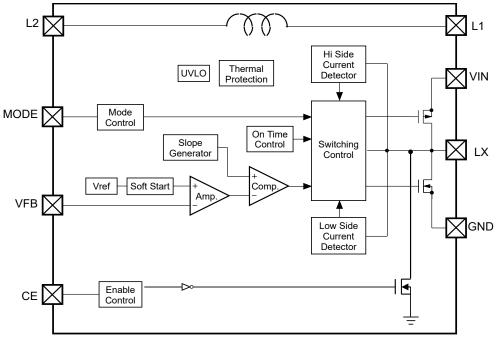
RM590Lxx2B Block Diagram

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### RM590L002C/D (Adjustable Output Voltage Type)

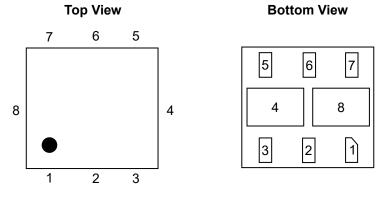
RM590L002C Block Diagram



RM590L002D Block Diagram

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# **PIN DESCRIPTIONS**



RM590L(QFN2220-8) Pin Configuration

#### RM590L (QFN2220-8) Pin Descriptions

Pin No.	Symbol	I/O	Description
1	VOUT/VFB	I	Output/Feedback Pin Fixed Output Voltage Type: Connect to V <sub>OUT</sub> pin and L2 pin. Adjustable Output Voltage Type: Receives the feedback voltage from a Resistive divider connected across the output. Refer to " <i>Adjustable</i> <i>Output Voltage Setting</i> "
2	LX	0	Switch Node Connection to the Inductor. This pin connects to the drains of the internal Main and synchronous power MOSFET switches.
3	MODE	I	Mode Select Input. To select forced PWM, connect this pin to a voltage above designated "High". Connecting this pin to a voltage between 0 V and designated "Low" selects PWM/VFM automatic shift operation mode.
4	L1	I	Inductor Pin 1 (Input pin of inductor built-in.) Connect this pin to Lx pin.
5	VIN	Ι	Power Input Supply. Decouple this pin to GND with a capacitor.
6	CE	I	Forcing this pin below designated "Low" level shuts down the RM590L. In shutdown all functions are disabled except auto discharge function. (option)
7	GND	I	Ground Pin
8	L2	0	Inductor Pin 2 (This pin connects to built-in inductor) Connect a capacitor between this pin and GND.

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# **ABSOLUTE MAXIMUM RATINGS**

Symbol	ltem	Ratings	Unit
VIN	Input Voltage	-0.3 to 6.5	V
V <sub>LX</sub>	LX / L1 / L2 Pin Voltage	-0.3 to V <sub>IN</sub> +0.3	V
Vce	CE Pin Voltage	-0.3 to 6.5	V
VMODE	MODE Pin Voltage	-0.3 to 6.5	V
Vout/Vfb	VOUT / VFB Pin Voltage	-0.3 to 6.5	V
ILX	LX-Pin Output Current	1.6	А
PD	Power Dissipation Refer to Appendix "POWER DISS		SSIPATION"
Tj	Junction Temperature Range	-40 to 125	°C
Tstg	Storage Temperature Range	-55 to 125	°C

#### ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the lifetime and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings are not assured.

# **ELECTROSTATIC DISCHARGE (ESD) RATINGS**

Symbol	Conditions	Ratings	Unit
V <sub>HBM</sub>	HBM C = 100pF, R = 1.5kΩ	-750 / +2000	V
Vcdm	CDM	± 1000	V

#### ELECTROSTATIC DISCHARGE RATINGS

The electrostatic discharge test is done based on JESD47.

In the HBM method, ESD is applied using the power supply pin and GND pin as reference pins.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Item	Ratings	Unit
VIN	Input Voltage	2.3 to 5.5	V
Та	Operating Temperature Range	-40 to 85	°C

#### **RECOMMENDED OPERATING CONDITIONS**

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such ratings by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

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# **ELECTRICAL CHARACTERISTICS**

The specifications surrounded by  $\square$  are guaranteed by design engineering at -40°C  $\leq$  Ta  $\leq$  85°C.

RM590Lx	x2A/B Electrical Characteristics				(Ta =	= 25°C)
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Vout	Output Voltage	$V_{IN} = V_{CE} = 3.6 V$ (V_{SET} $\leq 2.6 V$ ), $V_{IN} = V_{CE} = V_{SET} + 1 V$			x 1.015	V
		$(V_{SET} > 2.6 V)$ $V_{SET} < 1.2 V$	-0.018		+0.018	
fosc	Oscillator Frequency	$V_{IN} = V_{CE} = 3.6 \text{ V}, V_{SET} = 1.8 \text{ V},$ "Closed Loop Control"	4.8	6.0	7.2	MHz
IDD	Supply Current	$V_{IN} = V_{CE} = V_{OUT} = 3.6 V$ , $V_{MODE} = 0 V$		15		μA
ISTANDBY	Standby Current	$V_{IN} = 5.5 V, V_{CE} = 0 V$		0	5	μA
Ісен	CE "High" Input Current	$V_{IN} = V_{CE} = 5.5 V$	-1	0	1	μA
ICEL	CE "Low" Input Current	V <sub>IN</sub> = 5.5 V, V <sub>CE</sub> = 0 V	-1	0	1	μA
IMODEH	MODE "High" Input Current	$V_{IN} = V_{MODE} = 5.5 V$ , $V_{CE} = 0 V$	-1	0	1	μA
IMODEL	MODE "Low" Input Current	$V_{IN} = 5.5 V$ , $V_{CE} = V_{MODE} = 0 V$	-1	0	1	μA
Ivouth	Vout "High" Input Current	V <sub>IN</sub> = V <sub>OUT</sub> = 5.5 V, V <sub>CE</sub> = 0 V	-1	0	1	μA
IVOUTL	Vout "Low" Input Current	V <sub>IN</sub> = 5.5 V, V <sub>CE</sub> = V <sub>OUT</sub> = 0 V	-1	0	1	μA
RDISTR	Auto-discharge MOSFET On-resistance <sup>(1)</sup>	V <sub>IN</sub> = 3.6 V, V <sub>CE</sub> = 0 V		40		Ω
I <sub>LXLEAKH</sub>	LX "High" Leakage Current	$V_{IN} = V_{LX} = 5.5 \text{ V}, V_{CE} = 0 \text{ V}$	-1	0	5	μA
ILXLEAKL	LX "Low" Leakage Current	$V_{IN} = 5.5 V, V_{CE} = V_{LX} = 0 V$	-5	0	1	μA
$V_{CEH}$	CE "High" Input Voltage	V <sub>IN</sub> = 5.5 V	1.0			V
VCEL	CE "Low" Input Voltage	V <sub>IN</sub> = 2.3 V			0.4	V
VMODEH	MODE "High" Input Voltage	V <sub>IN</sub> = V <sub>CE</sub> = 5.5 V	1.0			V
V <sub>MODEL</sub>	MODE "Low" Input Voltage				0.4	V
Ronp	On-resistance of High Side MOSFET	$V_{IN} = 3.6 V$ , $I_{LX} = -100 mA$		0.245		Ω
RONN	On-resistance of Low Side MOSFET	V <sub>IN</sub> = 3.6 V, I <sub>LX</sub> = -100 mA		0.225		Ω
Maxduty	Maximum Duty Cycle		100			%
t <sub>start</sub>	Soft-start Time	$V_{IN} = V_{CE} = 3.6 V (V_{SET} \le 2.6 V),$ $V_{IN} = V_{CE} = V_{SET} + 1 V (V_{SET} > 2.6 V)$		150	300	μs
I <sub>LXLIM</sub>	LX Current Limit		600	1000		mA
VUVLO1	UVLO Threshold Voltage	V <sub>IN</sub> = V <sub>CE</sub> , Falling	1.85	2.00	2.20	V
$V_{\rm UVLO2}$		V <sub>IN</sub> = V <sub>CE</sub> , Rising	1.90	2.05	2.25	V

All test items listed under Electrical Characteristics are done under the pulse load condition (Tj  $\approx$  Ta = 25°C). Test circuit is operated with "Open Loop Control" (GND = 0 V), unless otherwise specified.

(1) RM590Lxx2B only

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The specifications surrounded by  $\square$  are guaranteed by design engineering at -40°C ≤ Ta ≤ 85°C.

(Ta = 25°C)
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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
VFB	Feedback Voltage	$V_{IN} = V_{CE} = 3.6 V$	0.591	0.600	0.609	V
fosc	Oscillator Frequency	V <sub>IN</sub> = V <sub>CE</sub> = 3.6 V, V <sub>SET</sub> = 1.8 V, "Closed Loop Control"	4.8	6.0	7.2	MHz
IDD	Supply Current	$V_{IN} = V_{CE} = V_{OUT} = 3.6 V$ , $V_{MODE} = 0 V$		15		μA
ISTANDBY	Standby Current	V <sub>IN</sub> = 5.5 V, V <sub>CE</sub> = 0 V		0	5	μA
Ісен	CE "High" Input Current	$V_{IN} = V_{CE} = 5.5 V$	-1	0	1	μA
ICEL	CE "Low" Input Current	V <sub>IN</sub> = 5.5 V, V <sub>CE</sub> = 0 V	-1	0	1	μA
I <sub>MODEH</sub>	MODE "High" Input Current	$V_{IN} = V_{MODE} = 5.5 V, V_{CE} = 0 V$	-1	0	1	μA
IMODEL	MODE "Low" Input Current	V <sub>IN</sub> = 5.5 V, V <sub>CE</sub> = V <sub>MODE</sub> = 0 V	-1	0	1	μA
Ivouth	V <sub>OUT</sub> "High" Input Current	$V_{IN} = V_{OUT} = 5.5 \text{ V}, V_{CE} = 0 \text{ V}$	-1	0	1	μA
IVOUTL	Vout "Low" Input Current	V <sub>IN</sub> = 5.5 V, V <sub>CE</sub> = V <sub>OUT</sub> = 0 V	-1	0	1	μA
Rdistr	Auto-discharge MOSFET On-resistance <sup>(1)</sup>	V <sub>IN</sub> = 3.6 V, V <sub>CE</sub> = 0 V		40		Ω
ILXLEAKH	LX "High" Leakage Current	$V_{IN} = V_{LX} = 5.5 \text{ V}, V_{CE} = 0 \text{ V}$	-1	0	5	μA
ILXLEAKL	LX "Low" Leakage Current	V <sub>IN</sub> = 5.5 V, V <sub>CE</sub> = V <sub>LX</sub> = 0 V	-5	0	1	μA
VCEH	CE "High" Input Voltage	V <sub>IN</sub> = 5.5 V	1.0			V
VCEL	CE "Low" Input Voltage	V <sub>IN</sub> = 2.3 V			0.4	V
VMODEH	MODE "High" Input Voltage	V <sub>IN</sub> = V <sub>CE</sub> = 5.5 V	1.0			V
VMODEL	MODE "Low" Input Voltage	$ V_{SET} \le 2.3 \text{ V}, V_{IN} = V_{CE} = 2.3 \text{ V} \\ V_{SET} > 2.3 \text{ V}, V_{IN} = V_{SET} $			0.4	V
Ronp	On-resistance of High Side MOSFET	$V_{IN} = 3.6 V$ , $I_{LX} = -100 mA$		0.245		Ω
Ronn	On-resistance of Low Side MOSFET	$V_{IN} = 3.6 V, I_{LX} = -100 mA$		0.225		Ω
Maxduty	Maximum Duty Cycle		100			%
<b>t</b> start	Soft-start Time			150	300	μs
Ilxlim	LX Current Limit		600	1000		mA
$V_{\text{UVLO1}}$		V <sub>IN</sub> = V <sub>CE,</sub> Falling	1.85	2.00	2.20	V
V <sub>UVLO2</sub>	UVLO Threshold Voltage	V <sub>IN</sub> = V <sub>CE</sub> , Rising	1.90	2.05	2.25	V

All test items listed under Electrical Characteristics are done under the pulse load condition (Tj  $\approx$  Ta = 25°C). Test circuit is operated with "Open Loop Control" (GND = 0 V), unless otherwise specified.

<sup>(1)</sup> RM590L002D only

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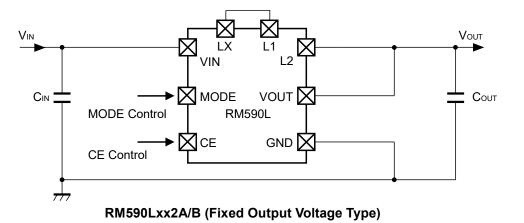
The specifications surrounded by  $\square$  are guaranteed by Design Engineering at  $-40^{\circ}C \le Ta \le 85^{\circ}C$ 

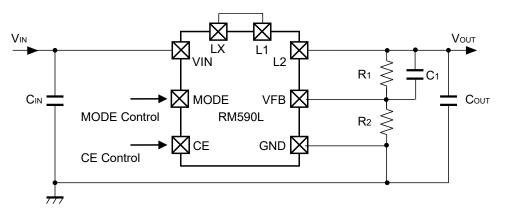
### RM590L series (Fixed Output Voltage Type) Product-specific Electrical Characteristics

Product Name		<b>V</b> OUT <b>[V]</b>	
Product Name	Min.	V <sub>SET</sub>	Max.
RM590L062x	0.582	0.600	0.618
RM590L072x	0.682	0.700	0.718
RM590L082x	0.782	0.800	0.818
RM590L092x	0.882	0.900	0.918
RM590L102x	0.982	1.000	1.018
RM590L102x5	1.032	1.050	1.068
RM590L112x	1.082	1.100	1.118
RM590L112x5	1.132	1.150	1.168
RM590L122x	1.182	1.200	1.218
RM590L132x	1.281	1.300	1.319
RM590L142x	1.379	1.400	1.421
RM590L152x	1.478	1.500	1.522
RM590L162x	1.576	1.600	1.624
RM590L172x	1.675	1.700	1.725
RM590L182x	1.773	1.800	1.827
RM590L192x	1.872	1.900	1.928
RM590L202x	1.970	2.000	2.030
RM590L212x	2.069	2.100	2.131
RM590L222x	2.167	2.200	2.233
RM590L232x	2.266	2.300	2.334
RM590L242x	2.364	2.400	2.436
RM590L252x	2.463	2.500	2.537
RM590L262x	2.561	2.600	2.639
RM590L272x	2.660	2.700	2.740
RM590L282x	2.758	2.800	2.842
RM590L292x	2.857	2.900	2.943
RM590L302x	2.955	3.000	3.045
RM590L312x	3.054	3.100	3.146
RM590L322x	3.152	3.200	3.248
RM590L332x	3.251	3.300	3.349

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# **TYPICAL APPLICATION CIRCUIT**





RM590L002C/D (Adjustable Output Voltage Type)

#### **Recommended External Components**

Symbol	Descriptions	
CIN	4.7 μF and more, Ceramic Capacitor	
Cout	10 μF, Ceramic Capacitor	

### Precautions for the Selection of External Parts

- The RM590L has a built-in inductor with L=0.5 $\mu$ H and DCR=0.125 $\Omega$  (TYP).
- Choose a low ESR ceramic capacitor. The capacitance of C<sub>IN</sub> between VIN and GND should be more than or equal to 4.7 μF. The capacitance of a ceramic capacitor (C<sub>OUT</sub>) should be 10 μF. Also, choose the capacitor with consideration for bias characteristics and input/output voltages.

# **OPERATION**

### **Chip Enable Function**

Forcing above designated "High" voltage to CE pin, the RM590L becomes active. Forcing below designated "Low" voltage to CE pin shuts down the RM590L. In shutdown (Standby) condition, all functions are disabled except Auto Discharge function. (Option) With Auto-Discharge option, the MOSFET to discharge the output capacitor turns on and the output is pulled down to GND. Without Auto-Discharge option, the output becomes "Hi-Z". CE pin can accept input range voltage regardless of the input of VIN pin. If Chip Enable function is not necessary, tie CE pin to VIN pin or other designated "High" voltage node at start-up.

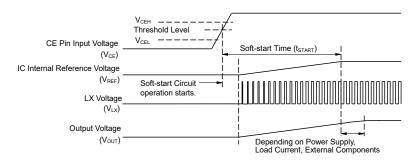
### Soft-start Time

### Starting-up with CE Pin

The IC starts to operate when the CE pin voltage ( $V_{CE}$ ) exceeds the threshold voltage. The threshold voltage is preset between CE "High" input voltage ( $V_{CEH}$ ) and CE "Low" input voltage ( $V_{CEL}$ ).

After the start-of the start-up of the IC, soft-start circuit starts to operate. Then, after a certain period of time, the reference voltage ( $V_{REF}$ ) in the IC gradually increases up to the specified value.

Notes: Soft start time  $(t_{START})^{(1)}$  is not always equal to the turn-on speed of the step-down DC/DC module. Please note that the turn-on speed could be affected by the power supply capacity, the output current, the inductance value and the C<sub>OUT</sub> value.



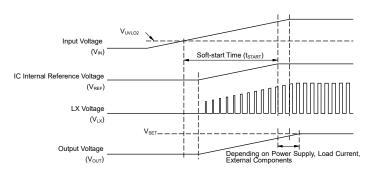
Timing Chart when Starting-up with CE Pin

<sup>&</sup>lt;sup>(1)</sup> Soft-start time (t<sub>START</sub>) indicates the duration until the reference voltage (V<sub>REF</sub>) reaches the specified voltage after soft-start circuit's activation.

### Starting-up with Power Supply

After the power-on, when  $V_{IN}$  exceeds the UVLO released voltage ( $V_{UVLO2}$ ), the IC starts to operate. Then, softstart circuit starts to operate and after a certain period of time,  $V_{REF}$  gradually increases up to the specified value.

Notes: Please note that the turn-on speed of  $V_{OUT}$  could be affected by the power supply capacity, the output current, the inductance value, the  $C_{OUT}$  value and the turn-on speed of  $V_{IN}$  determined by  $C_{IN}$ .



Timing Chart when Starting-up with Power Supply

### Auto Discharge Function

When turned off, the Vout voltage drops rapidly to near 0V by discharging the charge stored in the output capacitor through the MOSFET connected between the LX and GND pins. The auto discharge function is enabled when the CE pin = "low" or the thermal shutdown detection or the UVLO detection. On-resistance of MOSFET is Typ.  $40\Omega$ . This function may be required to meet the required sequence for electronic components powered by this device.

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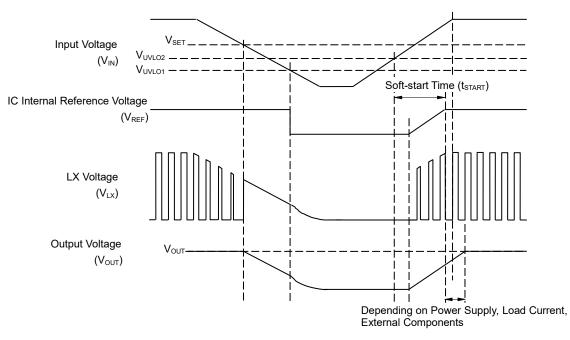
### Undervoltage Lockout (UVLO) Circuit

If  $V_{IN}$  becomes lower than  $V_{SET}$ , the step-down DC/DC module stops the switching operation and ON duty becomes 100%, and then  $V_{OUT}$  gradually drops according to  $V_{IN}$ .

If the  $V_{IN}$  drops more and becomes lower than the UVLO detector threshold ( $V_{UVLO1}$ ), the UVLO circuit starts to operate,  $V_{REF}$  stops, and High Side and Low Side built-in MOSFETs turn "OFF". As a result,  $V_{OUT}$  drops according to the  $C_{OUT}$  capacitance value and the load.

To restart the operation,  $V_{IN}$  needs to be higher than  $V_{UVLO2}$ . The timing chart below shows the voltage shifts of  $V_{REF}$ ,  $V_{LX}$  and  $V_{OUT}$  when  $V_{IN}$  value is varied.

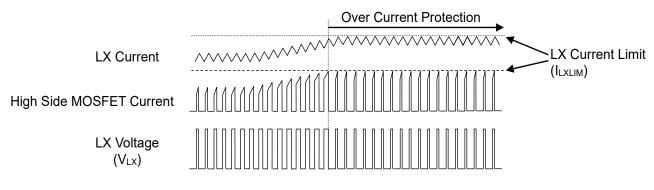
Notes: Falling edge (operating) and rising edge (releasing) waveforms of  $V_{OUT}$  could be affected by the initial voltage of  $C_{OUT}$  and the output current of  $V_{OUT}$ .



Timing Chart with Variations in Input Voltage (VIN)

### **Current limiting circuit**

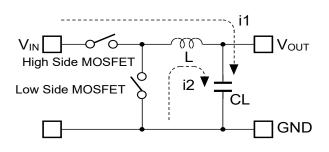
Current limit circuit supervises the inductor peak current (the peak current flowing through High Side MOSFET) in each switching cycle, and if the current exceeds the LX current limit ( $I_{LXLIM}$ ), it turns off High Side MOSFET  $I_{LXLIM}$  of the RM590L is set to Typ.1.0 A.

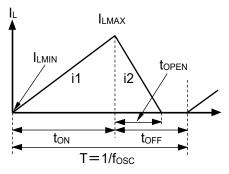


**Over-Current Protection Operation** 

### Operation of Step-down DC/DC module and Output Current

The step-down DC/DC module charges energy in the inductor when LX MOSFET turns "ON", and discharges the energy from the inductor when LX MOSFET turns "OFF" and controls with less energy loss, so that a lower output voltage ( $V_{OUT}$ ) than the input voltage ( $V_{IN}$ ) can be obtained. The operation of the step-down DC/DC module is explained in the following figures.





#### **Basic Circuit**

Inductor Current (IL) flowing through Inductor (L)

- Step1. High Side MOSFET turns "ON" and I<sub>L</sub> (i1) flows, L is charged with energy. At this moment, i1 increases from the minimum inductor current (I<sub>LMIN</sub>), which is 0 A, and reaches the maximum inductor current (I<sub>LMAX</sub>) in proportion to the on-time period (t<sub>ON</sub>) of High Side MOSFET.
- **Step2.** When High Side MOSFET turns "OFF", L tries to maintain  $I_L$  at  $I_{LMAX}$ , so L turns Low Side MOSFET "ON" and  $I_L$  (i2) flows into L.
- Step3. i2 decreases gradually and reaches I<sub>LMIN</sub> after the open-time period (t<sub>OPEN</sub>) of Low Side MOSFET, and then Low Side MOSFET turns "OFF". This is called discontinuous current mode. As the output current (I<sub>OUT</sub>) increases, the off-time period (t<sub>OFF</sub>) of High Side MOSFET runs out before I<sub>L</sub> reaches I<sub>LMIN</sub>. The next cycle starts, and High Side MOSFET turns "ON" and Low Side MOSFET turns "OFF", which means I<sub>L</sub> starts increasing from I<sub>LMIN</sub>. This is called continuous current mode.

In PWM mode,  $V_{OUT}$  is maintained by controlling  $t_{ON}$ . The oscillator frequency ( $f_{OSC}$ ) is maintained constant during PWM mode.

When the step-down DC/DC operation is constant,  $I_{LMIN}$  and  $I_{LMAX}$  during  $t_{ON}$  of High Side MOSFET would be same as during  $t_{OFF}$  of High Side MOSFET. The current differential between  $I_{LMAX}$  and  $I_{LMIN}$  is described as  $\Delta I$ , as the following equation (1).

 $\Delta I = I_{LMAX} - I_{LMIN} = V_{OUT} \times t_{OPEN} / 0.5 = (V_{IN} - V_{OUT}) \times t_{ON} / 0.5 \cdots (1)$ 

The above equation is predicated on the following requirements.

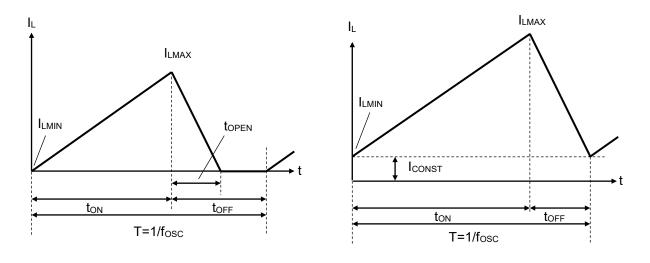
$$\begin{split} T &= 1 \; / \; f_{OSC} \; = t_{ON} \; + \; t_{OFF} \\ duty \; (\%) &= t_{ON} \; / \; T \; \times \; 100 \; = t_{ON} \; \times \; f_{OSC} \; \times \; 100 \\ t_{OPEN} &\leq t_{OFF} \end{split}$$

In Equation 1, "V<sub>OUT</sub> × t<sub>OPEN</sub> / 0.5" shows the amount of current change in "OFF" state. Also, "(V<sub>IN</sub> – V<sub>OUT</sub>) × t<sub>ON</sub> / L0.5" shows the amount of current change at "ON" state.

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#### **Discontinuous Mode and Continuous Mode**

As illustrated in Figure A., when  $I_{OUT}$  is relatively small,  $t_{OPEN} < t_{OFF}$ . In this case, the energy charged into L during  $t_{ON}$  will be completely discharged during  $t_{OFF}$ , as a result,  $I_{LMIN} = 0$ . This is called discontinuous mode. When  $I_{OUT}$  is gradually increased, eventually  $t_{OPEN} = t_{OFF}$  and when  $I_{OUT}$  is increased further, eventually  $I_{LMIN} > 0$  as illustrated in Figure B. This is called continuous mode.



#### Figure A. Discontinuous Mode

#### Figure B. Continuous Mode

In the continuous mode, the solution of Equation (1) is described as  $t_{ONC}$ .

 $t_{ONC} = T \times V_{OUT} / V_{IN}$ (2)

When  $t_{ON} < t_{ONC}$ , it is discontinuous mode, and when  $t_{ON} = t_{ONC}$ , it is continuous mode.

### Forced PWM Mode and VFM Mode

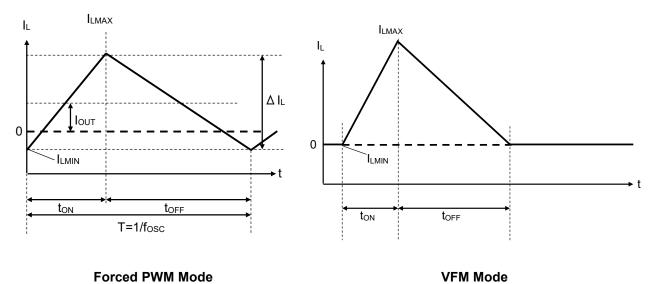
Output voltage controlling method is selectable between a forced PWM control type and a PWM/VFM autoswitching control type, and can be set by the MODE pin. The forced PWM control switches at fixed frequency rate in order to reduce noise in low output current. The PWM/VFM auto-switching control automatically switches from PWM mode to VFM mode in order to achieve high efficiency in low output current.

### Forced PWM Mode

By setting the MODE pin to "High", the IC switches the frequency at the fixed rate to reduce noise even when the output load is light. Therefore, when  $I_{OUT}$  is  $\Delta I_L/2$  or less,  $I_{LMIN}$  becomes less than "0". That is, the accumulated electricity in CL is discharged through the IC side while  $I_L$  is increasing from  $I_{LMIN}$  to "0" during  $t_{ON}$ , and also while  $I_L$  is decreasing from "0" to  $I_{LMIN}$  during  $t_{OFF}$ .

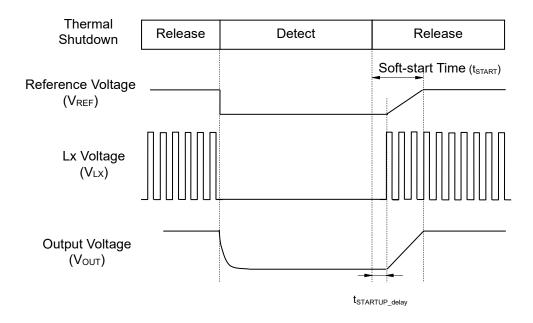
### VFM Mode

By setting the MODE pin to "Low", in low output current, the IC automatically switches into VFM mode in order to achieve high efficiency. In VFM mode,  $t_{ON}$  is determined depending on  $V_{IN}$  and  $V_{OUT}$ .



### **Thermal Shutdown Function**

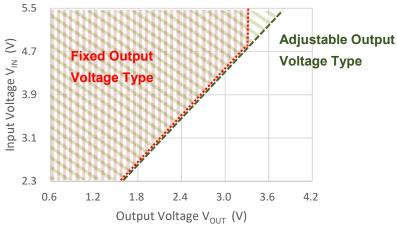
When the junction temperature exceeds the thermal shutdown detection temperature (Typ. 140°C), this IC cuts off the output and suppresses the self-heating. When the junction temperature falls below the thermal shutdown release temperature (Typ. 100°C), this IC will restart with the soft start operation.



# **TECHNICAL NOTES**

The performance of a power source circuit using this device is highly dependent on a peripheral circuit. A peripheral component or the device mounted on PCB should not exceed its rated voltage, rated current or rated power. When designing a peripheral circuit, please be fully aware of the following points.

- Set the external components as close as possible to the IC and minimize the wiring between the components and the IC. Especially, place a capacitor (C<sub>IN</sub>) as close as possible to the VIN pin and GND.
- Ensure the VIN and GND lines are sufficiently robust. If their impedance is too high, noise pickup or unstable operation may result.
- A large switching current flows through the VIN line, GND line, VOUT line, inductor, LX, L1 and L2. Make the wirings short and wide.
- For any setting type of output voltage, the input/output voltage ratio must meet the following requirement to achieve a stable VFM mode at light load when the MODE pin is "Low" (at PWM/VFM Auto Switching) :  $V_{OUT} / V_{IN} < 0.7$



V<sub>MODE</sub> = "Low", PWM / VFM Auto Switching

Available Voltage Area with Stable VFM Mode

- The thermal shutdown function is to prevent smoke and ignition of the IC, not to ensure the reliability of the IC or to keep it below the absolute maximum rating. In addition, it is not effective against heat generated when the IC is not operating normally, such as latch-up and overvoltage application.
- Do not design with depending on the thermal shutdown function of this IC as the system protection. The thermal shutdown function is designed for this IC.
- ESD Control

Take appropriate precautions when handling this product or PCB included this product.

Ex.

- Use of an antistatic wrist band
- Use of an ionizer

# **APPLICATION INFORMATION**

# Adjustable Output Voltage Setting (RM590L002C/D)

By connecting divider resistors (R1, R2) to the VFB pin, the set output voltage ( $V_{SET}$ ) can be set using the following equation.

 $V_{SET}$  =  $V_{FB} \times (R1 + R2) / R2$ 

The reference voltage ( $V_{FB}$ ) of this IC is set to 0.6 V, and the accuracy of  $V_{FB}$  and the output voltage setting range are as follows.

 $V_{\text{SET}}: 0.6V \le V_{\text{SET}} \le 5.5 \text{ V}$  $V_{\text{FB}}: 0.6 \text{ V} \pm 9\text{mV}$ 

Refer to the following table for the recommended values for R1, R2 and C1.

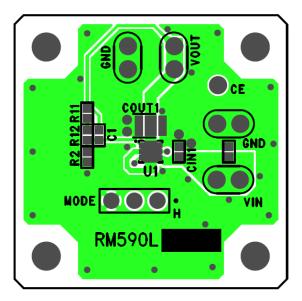
<b>V</b> <sub>SET</sub> <b>[V]</b>	R1 [kΩ]	R2 [kΩ]	C1 [pF]	
0.6	0	220	Open	
$0.6 < V_{SET} \le 0.9$		220	47	
$0.9 < V_{SET} \le 1.8$		220	33	
1.8 < V <sub>SET</sub> ≤ 2.1		150	10	
2.1 < V <sub>SET</sub> ≤ 2.4	R1 = (V <sub>SET</sub> / V <sub>FB</sub> -1) x R2	100	10	
$2.4 < V_{SET} \le 2.7$		68	10	
$2.7 < V_{SET} \le 3.0$		47	10	
$3.0 < V_{SET} \leq V_{IN}$		47	6.8	

#### Set Output Voltage (V<sub>SET</sub>) vs. R1 / R2 / C1 (Adjustable Output Voltage Type)

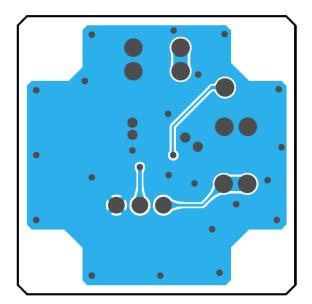
No.EA-592-231209

# PCB Layout

RM590L (QFN2220-8) Board Diagram



Top Layer

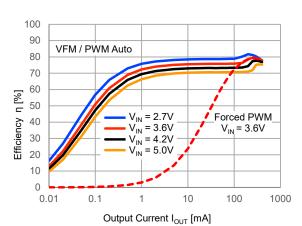


**Bottom Layer** 

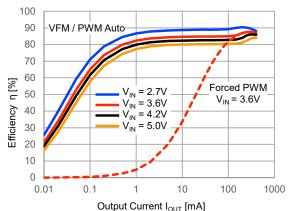
#### **TYPICAL CHARACTERISTICS**

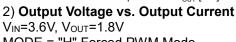
Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed. 1) **Efficiency vs. Output Current** 

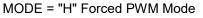
**V<sub>OUT</sub>=0.9V** 

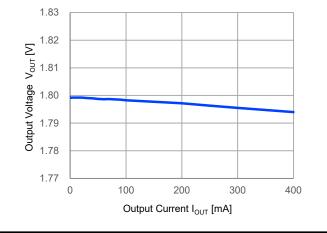




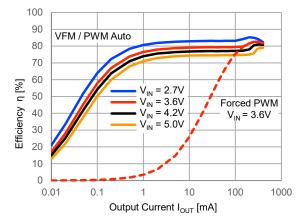




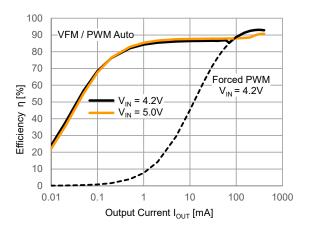




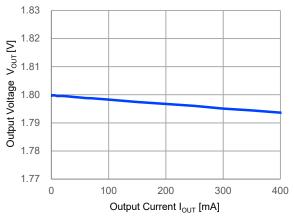




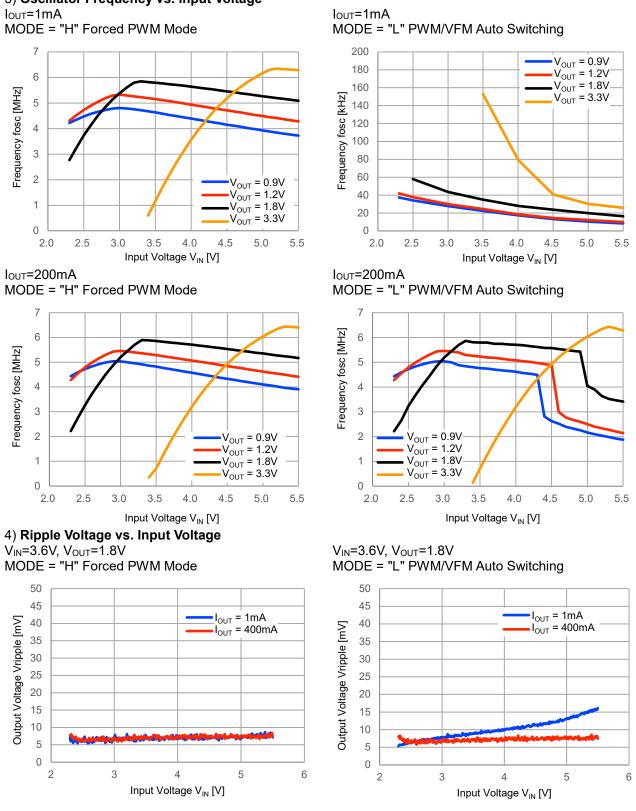




V<sub>IN</sub>=3.6V, V<sub>OUT</sub>=1.8V MODE = "L" PWM/VFM Auto Switching

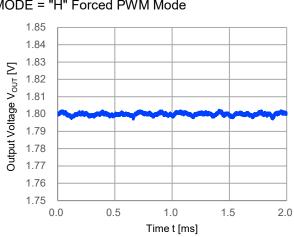


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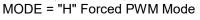


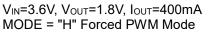
3) Oscillator Frequency vs. Input Voltage

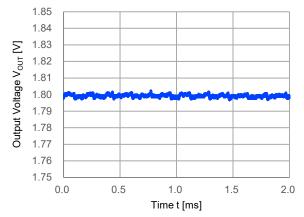
No.EA-592-231209



#### 5) Output Voltage Waveform VIN=3.6V, VOUT=1.8V, IOUT=1mA

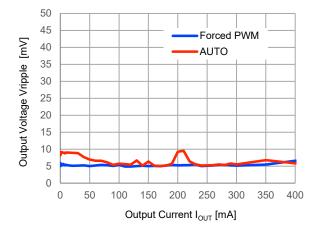


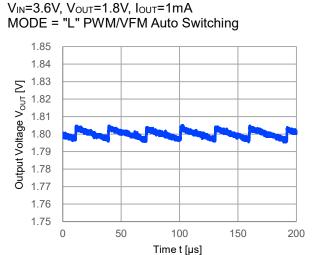


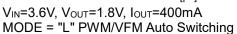


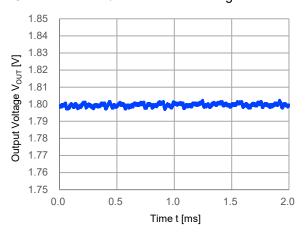
### 6) Ripple Voltage vs. Output Current VIN=3.6V, VOUT=1.8V

MODE = "L" PWM/VFM Auto Switching, MODE = "H" Forced PWM Mode



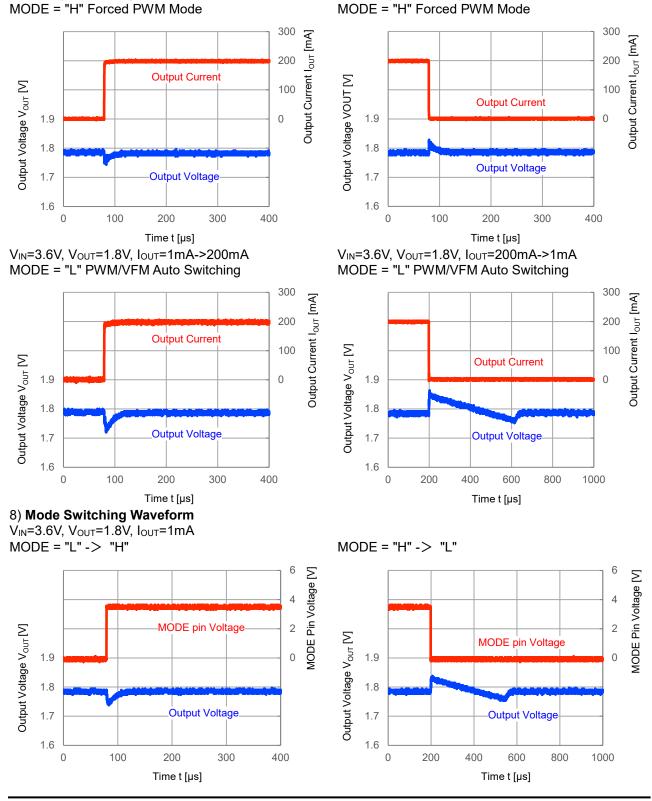






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VIN=3.6V, VOUT=1.8V, IOUT=200mA->1mA



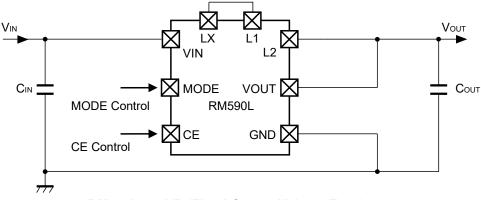
7) Load Transient Response Waveform VIN=3.6V, VOUT=1.8V, IOUT=1mA->200mA

Nisshinbo Micro Devices Inc.

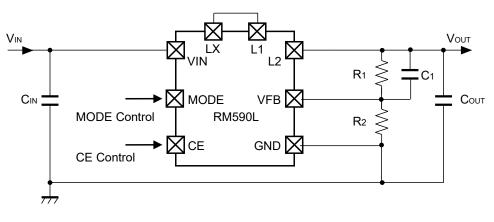
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### **Test Circuit**







# RM590L002C/D (Adjustable Output Voltage Type)

### Components list for our evaluation

Symbol	Specification	Maximum Ratings	Model
CIN	4.7µF	6.3V	C1005X5R0J475M050BC
Соит	10uF	6.3V	GRM155R60J106ME44D

# POWER DISSIPATION

# QFN2220-8

PD-QFN2220-8(85125)-JE-A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51.

#### **Measurement Conditions**

ltem	Measurement Conditions
Environment	Mounting on Board (Wind Velocity = 0 m/s)
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)
Board Dimensions	76.2 mm × 114.3 mm × 1.6 mm
Copper Ratio	Outer Layer (First Layer): More than 90% of 74.2 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 74.2 mm Square Outer Layer (Fourth Layer): More than 90% of 74.2 mm Square
Through-holes	φ 0.3 mm × 4 pcs

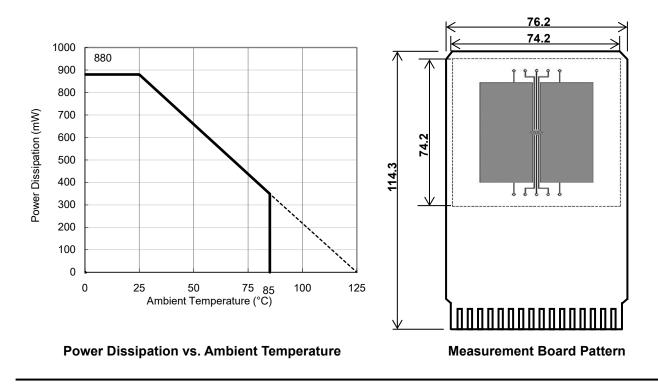
#### **Measurement Result**

(Ta = 25°C, Tjmax = 125°C)

Item	Measurement Result
Power Dissipation	880 mW
Thermal Resistance (θja)	θja = 113°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 55°C/W

θja: Junction-to-Ambient Thermal Resistance

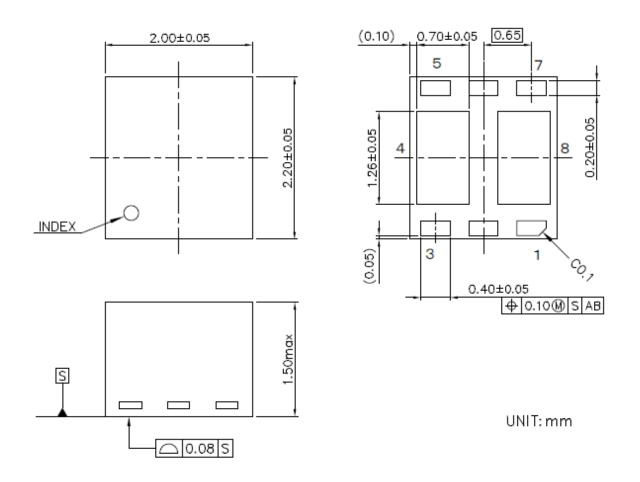
wjt: Junction-to-Top Thermal Characterization Parameter



# PACKAGE DIMENSIONS

# QFN2220-8

DM-QFN2220-8-JE-A



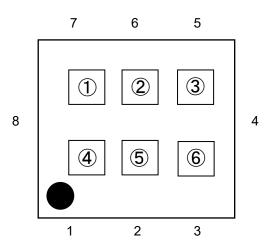
QFN2220-8 Package Dimensions

# PART MARKINGS

# **RM590L**

MK-RM590L-JAEA-A

①②③④: Product Code … Refer to *Part Marking List*⑤⑥: Lot Number … Alphanumeric Serial Number



#### QFN2220-8 Part Markings

#### NOTICE

There can be variation in the marking when different AOI (Automated Optical Inspection) equipment is used. In the case of recognizing the marking characteristic with AOI, please contact our sales or distributor before attempting to use AOI.

# PART MARKINGS

# **RM590L**

MK-RM590L-JAEA-A

Product Name	0234	Vout	Type) Part Marking List Product Name	0234	Vout
RM590L062A	101A	0.6 V	RM590L062B	301B	0.6 V
RM590L072A	102A	0.7 V	RM590L072B	302B	0.7 V
RM590L082A	103A	0.8 V	RM590L082B	303B	0.8 V
RM590L092A	104A	0.9 V	RM590L092B	304B	0.9 V
RM590L102A	105A	1.0 V	RM590L102B	305B	1.0 V
RM590L102A5	115A	1.05 V	RM590L102B5	306B	1.05 \
RM590L112A	106A	1.1 V	RM590L112B	307B	1.1 V
RM590L112A5	107A	1.15 V	RM590L112B5	308B	1.15 \
RM590L122A	108A	1.2 V	RM590L122B	309B	1.2 V
RM590L132A	109A	1.3 V	RM590L132B	310B	1.3 V
RM590L142A	110A	1.4 V	RM590L142B	311B	1.4 V
RM590L152A	111A	1.5 V	RM590L152B	312B	1.5 V
RM590L162A	112A	1.6 V	RM590L162B	313B	1.6 V
RM590L172A	113A	1.7 V	RM590L172B	314B	1.7 V
RM590L182A	114A	1.8 V	RM590L182B	315B	1.8 V
RM590L192A	201A	1.9 V	RM590L192B	401B	1.9 V
RM590L202A	202A	2.0 V	RM590L202B	402B	2.0 V
RM590L212A	203A	2.1 V	RM590L212B	403B	2.1 V
RM590L222A	204A	2.2 V	RM590L222B	404B	2.2 V
RM590L232A	205A	2.3 V	RM590L232B	405B	2.3 V
RM590L242A	206A	2.4 V	RM590L242B	406B	2.4 V
RM590L252A	207A	2.5 V	RM590L252B	407B	2.5 V
RM590L262A	208A	2.6 V	RM590L262B	408B	2.6 V
RM590L272A	209A	2.7 V	RM590L272B	409B	2.7 V
RM590L282A	210A	2.8 V	RM590L282B	410B	2.8 V
RM590L292A	211A	2.9 V	RM590L292B	411B	2.9 V
RM590L302A	212A	3.0 V	RM590L302B	412B	3.0 V
RM590L312A	213A	3.1 V	RM590L312B	413B	3.1 V
RM590L322A	214A	3.2 V	RM590L322B	414B	3.2 V
RM590L332A	215A	3.3 V	RM590L332B	415B	3.3 V

#### RM590Lxx2A / RM590Lxx2B (Fixed Output Voltage Type) Part Marking List

# RM590L002C / RM590L002D (Adjustable Output Voltage Type) Part Marking List

Product Name	0234	Product Name	$\bigcirc \bigcirc $
RM590L002C	5 0 1 C	RM590L002D	6 0 1 D

- 1. The products and the product specifications described in this document are subject to change or discontinuation of production without notice for reasons such as improvement. Therefore, before deciding to use the products, please refer to our sales representatives for the latest information thereon.
- 2. The materials in this document may not be copied or otherwise reproduced in whole or in part without the prior written consent of us.
- 3. This product and any technical information relating thereto are subject to complementary export controls (so-called KNOW controls) under the Foreign Exchange and Foreign Trade Law, and related politics ministerial ordinance of the law. (Note that the complementary export controls are inapplicable to any application-specific products, except rockets and pilotless aircraft, that are insusceptible to design or program changes.) Accordingly, when exporting or carrying abroad this product, follow the Foreign Exchange and Foreign Trade Control Law and its related regulations with respect to the complementary export controls.
- 4. The technical information described in this document shows typical characteristics and example application circuits for the products. The release of such information is not to be construed as a warranty of or a grant of license under our or any third party's intellectual property rights or any other rights.
- 5. The products listed in this document are intended and designed for use as general electronic components in standard applications (office equipment, telecommunication equipment, measuring instruments, consumer electronic products, amusement equipment etc.). Those customers intending to use a product in an application requiring extreme quality and reliability, for example, in a highly specific application where the failure or misoperation of the product could result in human injury or death should first contact us.
  - Aerospace Equipment
  - Equipment Used in the Deep Sea
  - Power Generator Control Equipment (nuclear, steam, hydraulic, etc.)
  - Life Maintenance Medical Equipment
  - Fire Alarms / Intruder Detectors
  - Vehicle Control Equipment (automotive, airplane, railroad, ship, etc.)
  - Various Safety Devices
  - Traffic control system
  - Combustion equipment

In case your company desires to use this product for any applications other than general electronic equipment mentioned above, make sure to contact our company in advance. Note that the important requirements mentioned in this section are not applicable to cases where operation requirements such as application conditions are confirmed by our company in writing after consultation with your company.

- 6. We are making our continuous effort to improve the quality and reliability of our products, but semiconductor products are likely to fail with certain probability. In order to prevent any injury to persons or damages to property resulting from such failure, customers should be careful enough to incorporate safety measures in their design, such as redundancy feature, fire containment feature and fail-safe feature. We do not assume any liability or responsibility for any loss or damage arising from misuse or inappropriate use of the products.
- 7. The products have been designed and tested to function within controlled environmental conditions. Do not use products under conditions that deviate from methods or applications specified in this datasheet. Failure to employ the products in the proper applications can lead to deterioration, destruction or failure of the products. We shall not be responsible for any bodily injury, fires or accident, property damage or any consequential damages resulting from misuse or misapplication of the products.
- 8. Quality Warranty
  - 8-1. Quality Warranty Period

In the case of a product purchased through an authorized distributor or directly from us, the warranty period for this product shall be one (1) year after delivery to your company. For defective products that occurred during this period, we will take the quality warranty measures described in section 8-2. However, if there is an agreement on the warranty period in the basic transaction agreement, quality assurance agreement, delivery specifications, etc., it shall be followed.

8-2. Quality Warranty Remedies

When it has been proved defective due to manufacturing factors as a result of defect analysis by us, we will either deliver a substitute for the defective product or refund the purchase price of the defective product.

- Note that such delivery or refund is sole and exclusive remedies to your company for the defective product.
- 8-3. Remedies after Quality Warranty Period

With respect to any defect of this product found after the quality warranty period, the defect will be analyzed by us. On the basis of the defect analysis results, the scope and amounts of damage shall be determined by mutual agreement of both parties. Then we will deal with upper limit in Section 8-2. This provision is not intended to limit any legal rights of your company.

- 9. Anti-radiation design is not implemented in the products described in this document.
- 10. The X-ray exposure can influence functions and characteristics of the products. Confirm the product functions and characteristics in the evaluation stage.
- 11. WLCSP products should be used in light shielded environments. The light exposure can influence functions and characteristics of the products under operation or storage.
- 12. Warning for handling Gallium and Arsenic (GaAs) products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
- 13. Please contact our sales representatives should you have any questions or comments concerning the products or the technical information.



Nisshinbo Micro Devices Inc.

Official website https://www.nisshinbo-microdevices.co.jp/en/ Purchase information https://www.nisshinbo-microdevices.co.jp/en/buy/